ABSTRACT

INTEGRATED CIRCUIT PROCESSING SYSTEM

An integrated circuit processing system is provided including providing a substrate having an integrated circuit, forming an interconnect layer over the integrated circuit, applying a low-K dielectric layer over the interconnect layer, applying an ultra low-K dielectric layer over the low-K dielectric layer, forming an opening through the ultra low-K dielectric layer and the low-K dielectric layer to the interconnect layer, depositing an interconnect metal in the opening, and chemical-mechanical polishing the interconnect metal and the ultra low-K dielectric layer.

FIGURE 1